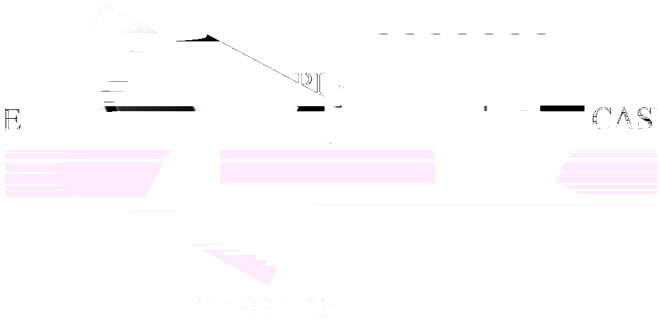
S1D015120A

TriQSiC™ 1200V Silicon Carbide Schottky Diode

Features

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-
-
-
-
-
-



Benefits

-
-
-
-
-

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{RRM}	I_F	Q_C	Marking	Package

Table of contents

Features 1

Benefits 1

Applications 1

Table of contents 2

1 Maximum ratings 3

2 Thermal characteristics 3

3 Electrical characteristics 4

4 Electrical characteristic diagrams 5

5 Package drawing (TO-220-2L) 7

Revision history 8

Attention 8

S1D015120A

1200V SiC Schottky Diode

1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note

2 Thermal characteristics

Table 3 Thermal characteristics

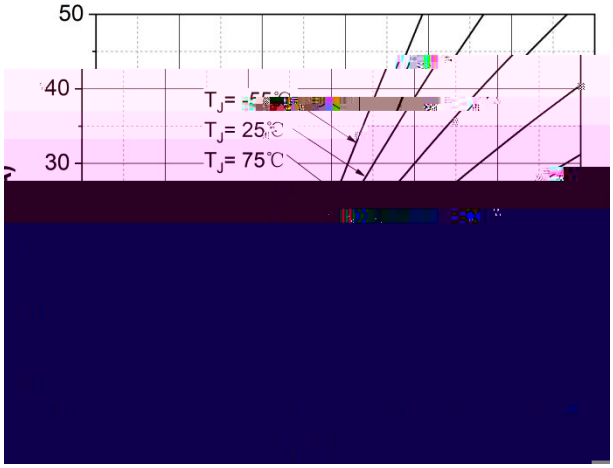
Symbol	Parameter	Typ.	Unit	Test Conditions	Note

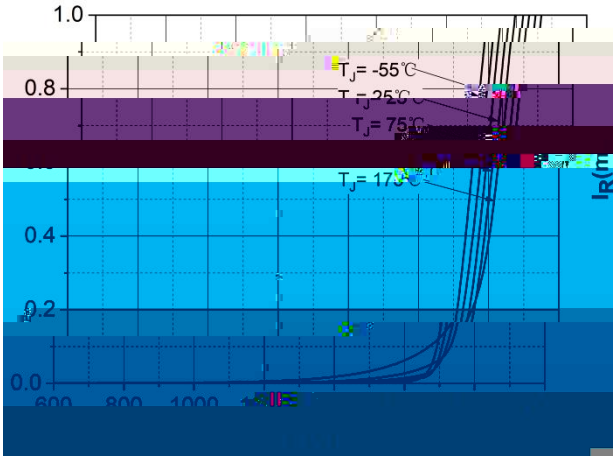
3 Electrical characteristics

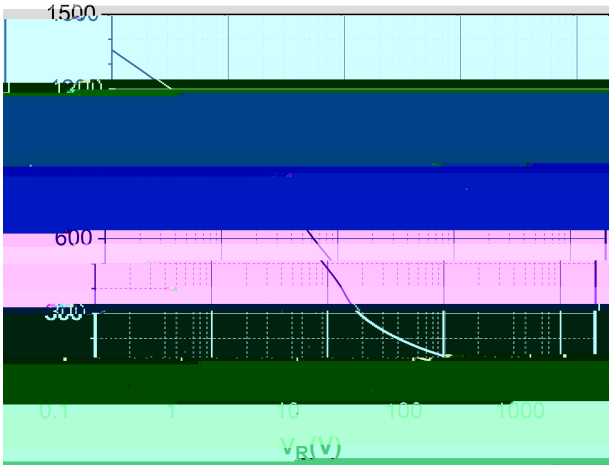
Table 4 Electrical characteristics

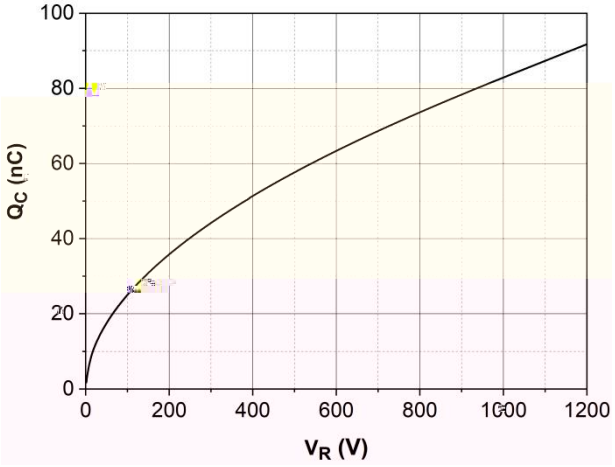
Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note

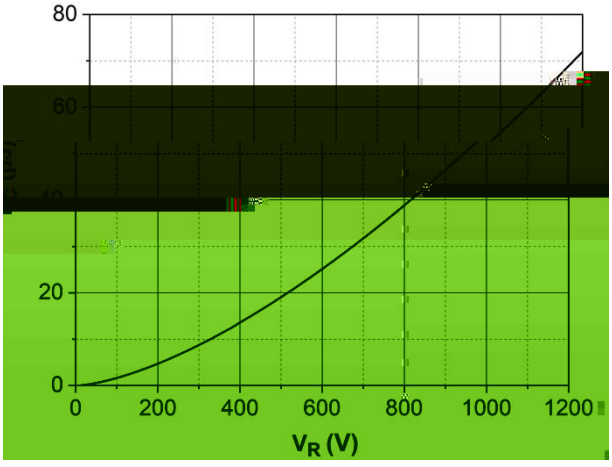
4 Electrical characteristic diagrams

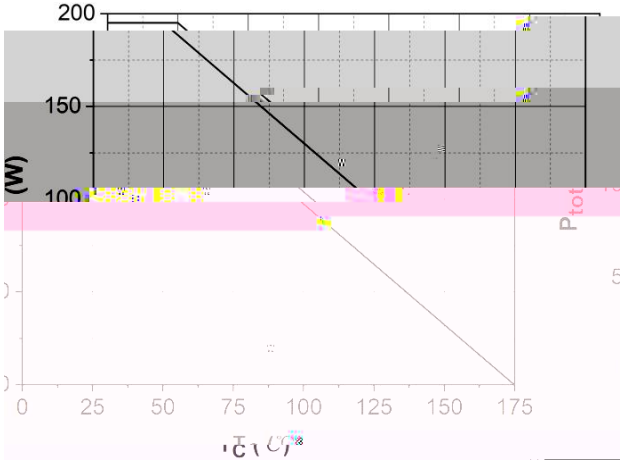




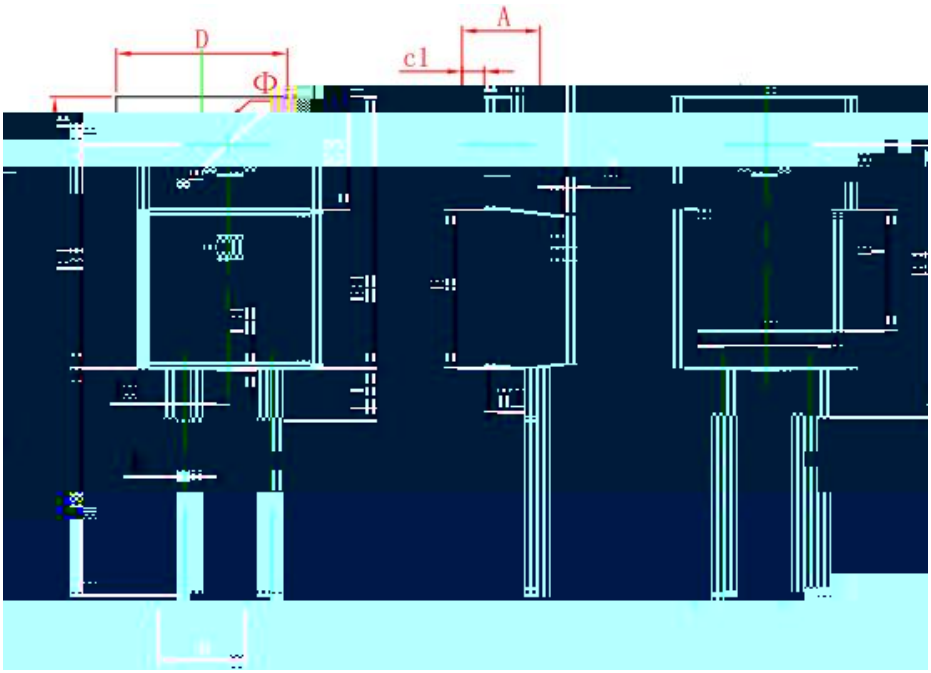








5 Package drawing



Symbol	Dimensions in Millimeters	
	Min.	Max.
A	4.400	4.600
A1	2.250	2.550
b	0.710	0.910
b1	1.170	1.370
c	0.330	0.650
c1	1.200	1.400
D	9.910	10.250
E	8.950	9.750
E1	12.700	13.000
E2	15.500	15.800
E3	6.350	6.650
E4	15.750	16.050
e	4.980	5.180
F	2.650	2.950

S1D015120A

1200V SiC Schottky Diode

Revision history

Document version	Date of release	Document stage	Description of changes
V02_00	2026-01-13	Final	——

Attention

RoHS compliance

REACH compliance

S1D015120A